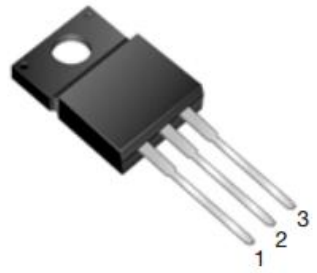
Technical Data
Data Sheet N0131, Rev. D

MBRF20200CT (CTR) SCHOTTKY RECTIFIER

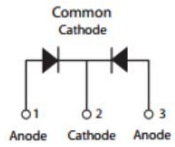


ITO-220AB

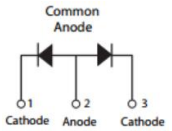
Features

- 175˚C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



MBRF20200CT



MBRF20200CTR

Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	-	200	V
Average Rectified Forward Current	$I_{F(AV)}$	50% duty cycle @Tc=105˚C, rectangular wave form	10(Per Leg) 20(Per Device)	A
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I_{FSM}	8.3ms, Half Sine pulse	150	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop(Per Leg)*	V_{F1}	@10A, Pulse, T_J = 25 ˚C	0.85	0.95	V
	V_{F2}	@10A, Pulse, T_J = 125 ˚C	0.75	0.85	V
Reverse Current(Per Leg)*	I_{R1}	@V_R = rated V_R, T_J = 25 ˚C	0.001	1.0	mA
	I_{R2}	@V_R = rated V_R, T_J = 125 ˚C	0.03	50	mA
Junction Capacitance(Per Leg)	C_T	@V_R = 5V, T_C = 25 ˚C, f_{SIG} = 1MHz	110	300	pF
Series Inductance(Per Leg)	L_S	Measured lead to lead 5 mm from package body	8.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs
RSM Isolation Voltage (t = 1.0 second, R. H. < =30%, T_A = 25 ˚C)	V_{ISO}	Clip mounting, the epoxy body away from the heatsink edge by more than 0.110" along the lead direction.	-	4500	V
		Clip mounting, the epoxy body is inside the heatsink.	-	3500	
		Screw mounting, the epoxy body is inside the heatsink.	-	1500	

* Pulse width < 300 μs, duty cycle < 2%

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Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +175	˚C
Storage Temperature	T_{stg}	-	-55 to +175	˚C
Typical Thermal Resistance Junction to Case	$R_{\theta JC}$	DC operation	4.5	˚C/W
Approximate Weight	wt	-	2	g
Case Style	ITO-220AB			

Ratings and Characteristics Curves

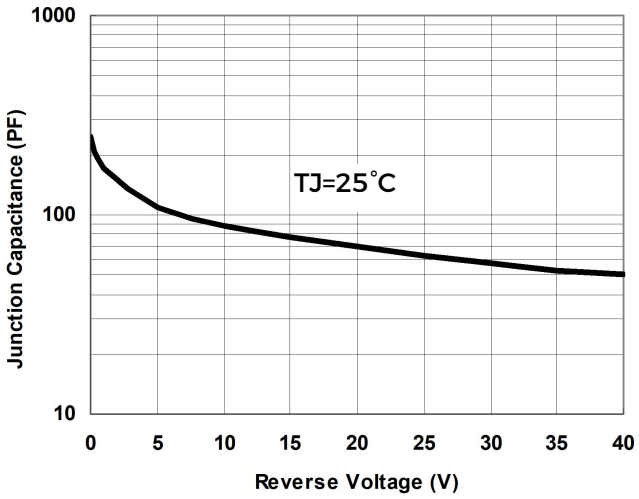

Fig.1-Typical Junction Capacitance

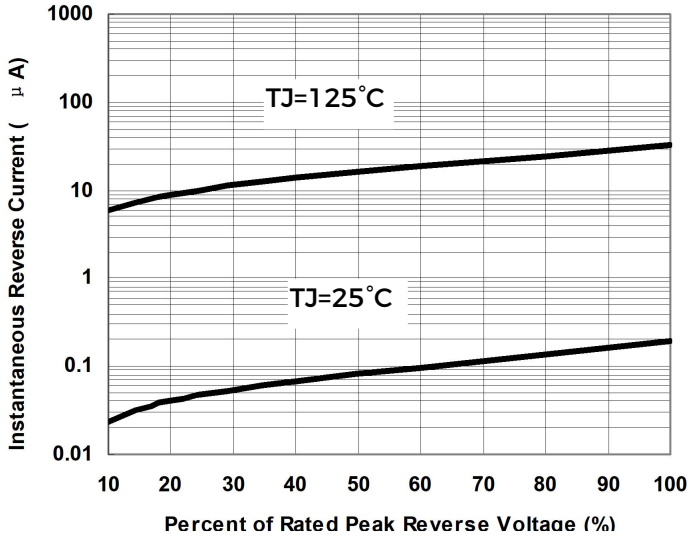

Fig.2-Typical Reverse Characteristics

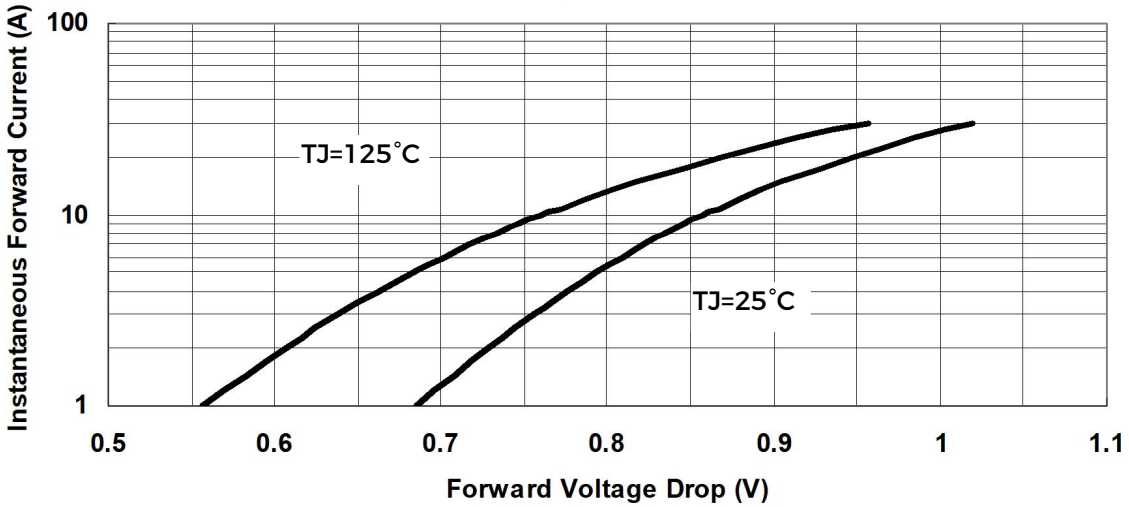

Fig.3-Typical Instantaneous Forward Voltage Characteristics

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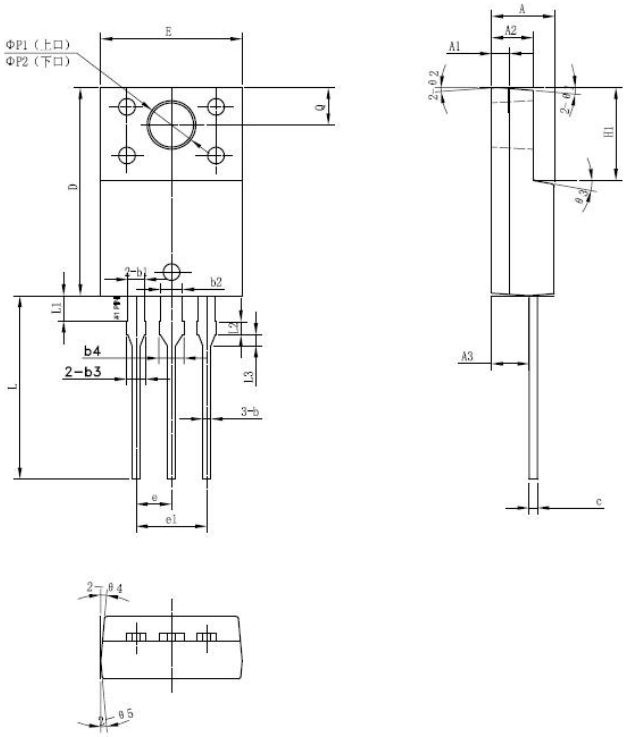
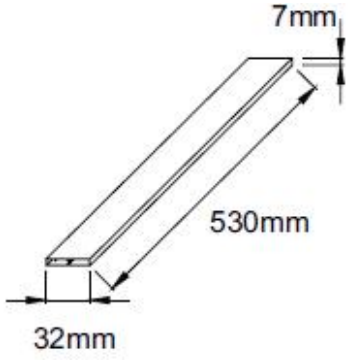
Mechanical Dimensions ITO-220AB

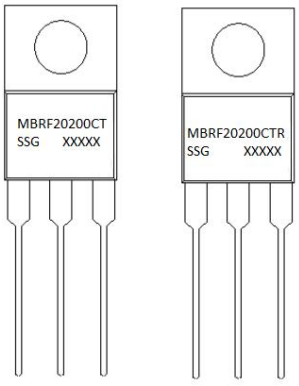


SYMBOL	Millimeters		
	MIN.	TYP.	MAX.
A	4.30	4.50	4.70
A1	1.10	1.30	1.50
A2	2.80	3.00	3.20
A3	2.50	2.70	2.90
b	0.50	0.60	0.75
b1	1.10	1.20	1.35
b2	1.50	1.60	1.75
b3	1.20	1.30	1.45
b4	1.60	1.70	1.85
c	0.50	0.60	0.75
D	14.80	15.00	15.20
E	9.96	10.16	10.36
e		2.55	
e1		5.10	
H1	6.50	6.70	6.90
L	12.70	13.20	13.70
L1	1.60	1.80	2.00
L2	0.80	1.00	1.20
L3	0.60	0.80	1.00
ΦP1(上口)	3.30	3.50	3.70
ΦP2(下口)	2.99	3.19	3.39
Q	2.50	2.70	2.90
Θ1		5°	
Θ2		4°	
Θ3		10°	
Θ4		5°	
Θ5		5°	

Tube Specification



Marking Diagram



Where XXXXX is YYWWL

MBR	= Device Type
F	= Package type
20	= Forward Current (20A)
200	= Reverse Voltage (200V)
CT(CTR)	= Configuration
SSG	= SSG
YY	= Year
WW	= Week
L	= Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information

Device	Package	Shipping
MBRF20200CT(CTR)	ITO-220AB(Pb-Free)	50 pcs/ tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

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